#### TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL JUNCTION TYPE

# 2 S K 2 4 6

FOR CONSTANT CURRENT, IMPEDANCE

CONVERTER AND DC-AC HIGH INPUT

IMPEDANCE AMPLIFIER CIRCUIT APPLICATIONS

• High Breakdown Voltage :  $V_{GDS} = -50 V$ 

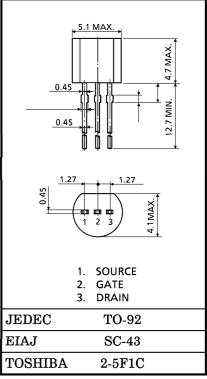
• High Input Impedance :  $I_{GSS} = -1 \text{ nA (Max.)}$ 

 $(V_{GS} = -30 V)$ 

## MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Gate-Drain Voltage	$v_{\mathrm{GDS}}$	-50	V
Gate Current	$I_{\mathbf{G}}$	10	mA
Drain Power Dissipation	$P_{\mathbf{D}}$	300	mW
Junction Temperature	$T_{j}$	125	$^{\circ}\mathrm{C}$
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~125	°C

Unit in mm



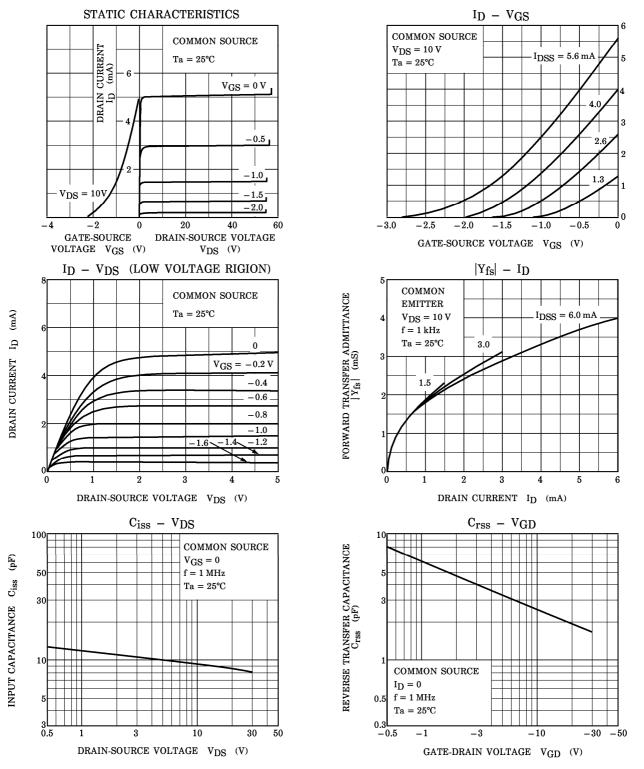
Weight: 0.21 g

### ELECTRICAL CHARACTERISTICS (Ta = 25°C)

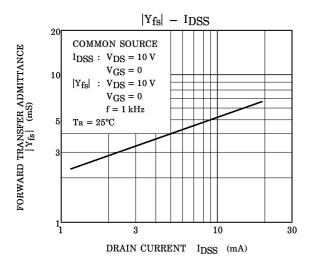
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Cut-off Current	$I_{ m GSS}$	$V_{GS} = -30 \text{ V}, V_{DS} = 0$	_	_	-1.0	nA
Gate-Drain Breakdown Voltage	V (BR) GDS	$V_{ m DS} = 0, \; I_{ m G} = -100 \; \mu { m A}$	-50	_	_	v
Drain Current	I <sub>DSS</sub> (Note)	$V_{DS} = 10 \text{ V}, \ V_{GS} = 0$	1.2	_	14	mA
Gate-Source Cut-off Voltage	V <sub>GS</sub> (OFF)	$V_{DS} = 10 \text{ V}, I_{D} = 0.1 \mu\text{A}$	-0.7	_	-6.0	V
Forward Transfer Admittance	Y <sub>fs</sub>	$ m V_{DS} = 10 \ V, \ V_{GS} = 0, \ f = 1 \ kHz$	1.5	_	_	mS
Input Capacitance	Ciss	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$ f = 1 MHz	_	9.0	_	pF
Reverse Transfer Capacitance	$\mathrm{C}_{\mathrm{rss}}$	$V_{ m DG} = 10   m V,  I_{ m D} = 0,  f = 1   m MHz$	_	2.5	_	pF

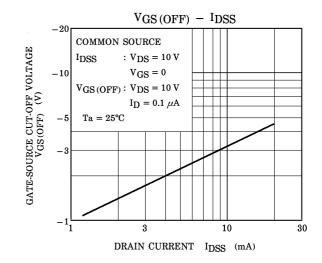
(Note) : IDSS Classification  $Y: 1.2\sim3.0 \text{ mA}, GR: 2.6\sim6.5 \text{ mA}, BL: 6\sim14 \text{ mA}$ 

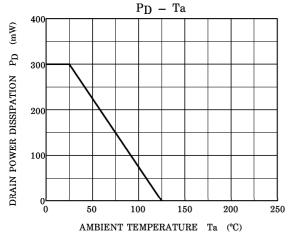
1 2001-05-31



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